

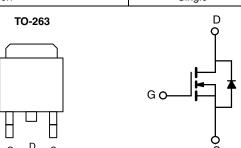
Top View

www.vishay.com

Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0035				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0039				
I _D (A)	120				
Configuration	Single				



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R_a and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N06-3m5L-GE3

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Currenta	T _C = 25 °C	1	120	
Continuous Drain Current	T _C = 125 °C	- I _D	120	
Continuous Source Current (Diode Conduc	tion) ^a	I _S	120	Α
Pulsed Drain Current ^b	I _{DM}	480		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	100	
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	500	mJ
M. C. D. Division	T _C = 25 °C	D	375	14/
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125	W
Operating Junction and Storage Temperatu	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				l		ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	900	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0028	0.0035	Ω	
Dunin Course On Chata Basistanas		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0064		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0080		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0031	0.0039		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	190	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	11 755	14 700	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	: -	1112	1400		
Reverse Transfer Capacitance	C _{rss}]		-	481	605		
Total Gate Charge ^c	Qg			-	220	330		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 110 \text{ A}$	-	35	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1			35	-	1	
Gate Resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	19	29		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_L = 0.27 \Omega$ $I_D \cong 110 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 2.5 \Omega$		-	23	35	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	83	125		
Fall Time ^c	t _f			-	35	53		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V _{SD}	$I_F = 50 \text{ A}, V_{GS} = 0$		_	0.8	1.5	V	

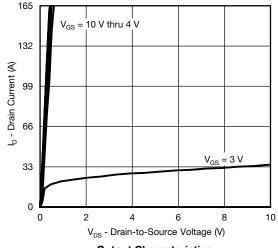
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

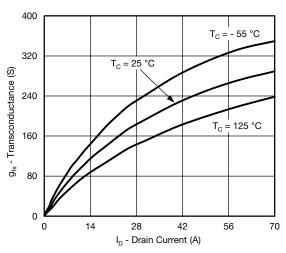
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



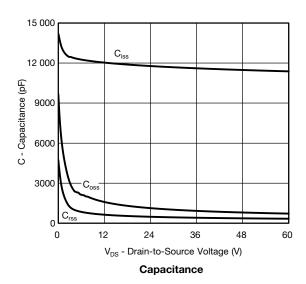
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

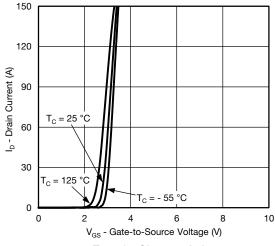


Output Characteristics

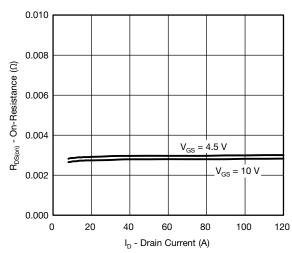


Transconductance

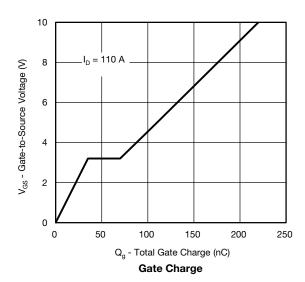




Transfer Characteristics

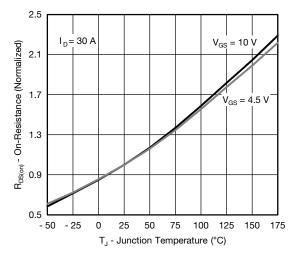


On-Resistance vs. Drain Current

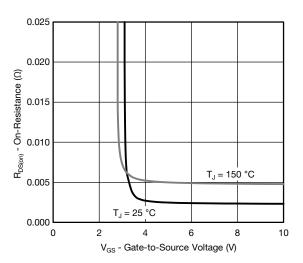




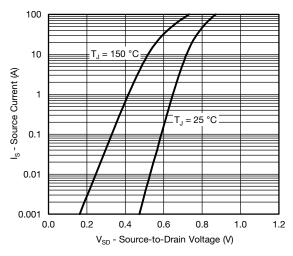
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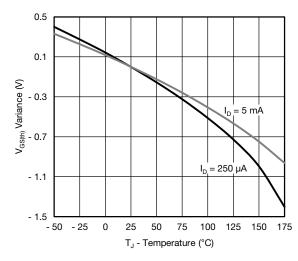
On-Resistance vs. Junction Temperature



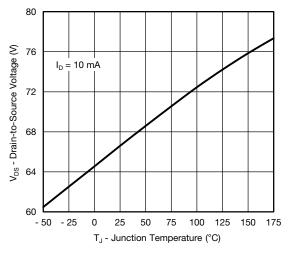
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage

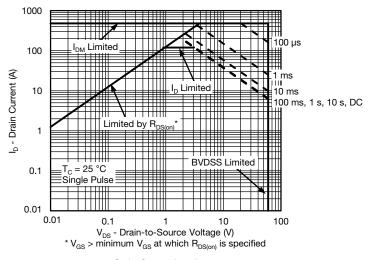


Threshold Voltage

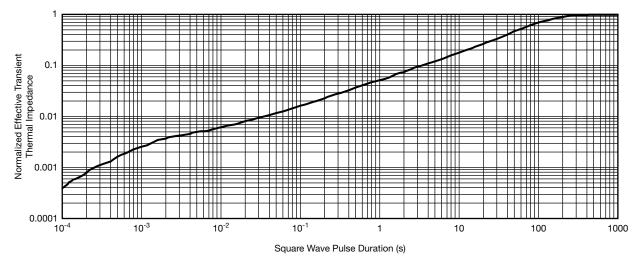


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



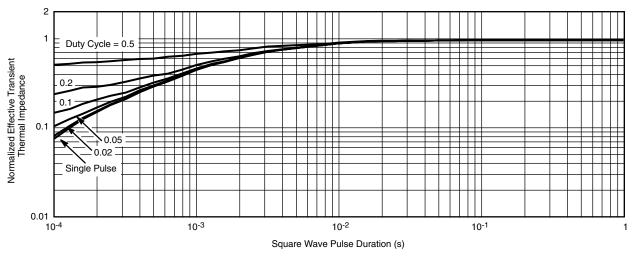
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg263814.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4 0.010		BSC	0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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